

Dual D-Type Flip-Flop with Set and Reset

The MC74VHC74 is an advanced high speed CMOS D-type flip-flop fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The signal level applied to the D input is transferred to Q output during the positive going transition of the Clock (CP) pulse.

Reset (\overline{RD}) and Set (\overline{SD}) are independent of the Clock (CP) and are accomplished by setting the appropriate input Low.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7V, allowing the interface of 5V systems to 3V systems.

- High Speed: $f_{max} = 170\text{MHz}$ (Typ) at $V_{CC} = 5\text{V}$
- Low Power Dissipation: $I_{CC} = 2\mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2V to 5.5V Operating Range
- Low Noise: $V_{OLP} = 0.8\text{V}$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; Machine Model > 200V
- Chip Complexity: 128 FETs or 32 Equivalent Gates

MC74VHC74



D SUFFIX
14-LEAD SOIC PACKAGE
CASE 751A-03



DT SUFFIX
14-LEAD TSSOP PACKAGE
CASE 948G-01



M SUFFIX
14-LEAD SOIC EIAJ PACKAGE
CASE 965-01

ORDERING INFORMATION

MC74VHCXXD	SOIC
MC74VHCXXDT	TSSOP
MC74VHCXXM	SOIC EIAJ

MC74VHC74

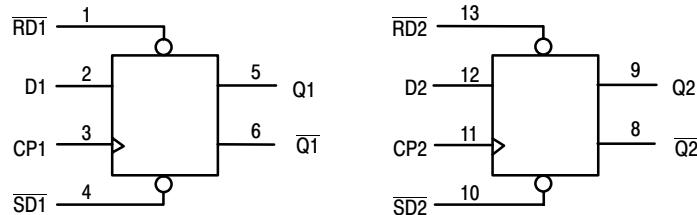


Figure 1. LOGIC DIAGRAM

$\overline{RD_1}$	1 •	14	V _{CC}
D1	2	13	$\overline{RD_2}$
CP1	3	12	D2
$\overline{SD_1}$	4	11	CP2
Q1	5	10	$\overline{SD_2}$
$\overline{Q1}$	6	9	Q2
GND	7	8	$\overline{Q2}$

Figure 2. PIN ASSIGNMENT

FUNCTION TABLE

Inputs				Outputs	
S _D	R _D	C _P	D	Q	\overline{Q}
L	H	X	X	H	L
H	L	X	X	L	H
L	L	X	X	H*	H*
H	H	✓	H	H	L
H	H	✓	L	L	H
H	H	L	X	No Change	
H	H	H	X	No Change	
H	H	✗	X	No Change	

*Both outputs will remain high as long as Set and Reset are low, but the output states are unpredictable if Set and Reset go high simultaneously.

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V _{CC}	DC Supply Voltage	– 0.5 to + 7.0	V
V _{in}	DC Input Voltage	– 0.5 to + 7.0	V
V _{out}	DC Output Voltage	– 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	– 20	mA
I _{OK}	Output Diode Current	± 20	mA
I _{out}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 50	mA
P _D	Power Dissipation in Still Air, SOIC Packages† TSSOP Package†	500 450	mW
T _{stg}	Storage Temperature	– 65 to + 150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

†Derating — SOIC Packages: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage	2.0	5.5	V
V _{in}	DC Input Voltage	0	5.5	V
V _{out}	DC Output Voltage	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	– 40	+ 85	°C
t _r , t _f	Input Rise and Fall Time V _{CC} = 3.3V ± 0.3V V _{CC} = 5.0V ± 0.5V	0 0	100 20	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = – 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	Minimum High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} × 0.7			1.50 V _{CC} × 0.7		V
V _{IL}	Maximum Low-Level Input Voltage		2.0 3.0 to 5.5				0.50 V _{CC} × 0.3		V
V _{OH}	Minimum High-Level Output Voltage V _{in} = V _{IH} or V _{IL} I _{OH} = – 50µA		2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
			V _{in} = V _{IH} or V _{IL} I _{OH} = – 4mA I _{OH} = – 8mA	3.0 4.5	2.58 3.94		2.48 3.80		
V _{OL}	Maximum Low-Level Output Voltage V _{in} = V _{IH} or V _{IL} I _{OL} = 50µA		2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1	0.1 0.1 0.1		V
			V _{in} = V _{IH} or V _{IL} I _{OL} = 4mA I _{OL} = 8mA	3.0 4.5			0.36 0.36		
							0.44 0.44		

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = - 40 to 85°C		Unit
				Min	Typ	Max	Min	Max	
I _{in}	Maximum Input Leakage Current	V _{in} = 5.5V or GND	0 to 5.5			± 0.1		± 1.0	µA
I _{CC}	Maximum Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			2.0		20.0	µA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = - 40 to 85°C		Unit
			Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, CP to Q or \bar{Q}	V _{CC} = 3.3 ± 0.3V C _L = 15pF C _L = 50pF		6.7 9.2	11.9 15.4	1.0 1.0	14.0 17.5	ns
		V _{CC} = 5.0 ± 0.5V C _L = 15pF C _L = 50pF		4.6 6.1	7.3 9.3	1.0 1.0	8.5 10.5	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, \bar{SD} or \bar{RD} to Q or \bar{Q}	V _{CC} = 3.3 ± 0.3V C _L = 15pF C _L = 50pF		7.6 10.1	12.3 15.8	1.0 1.0	14.5 18.0	ns
		V _{CC} = 5.0 ± 0.5V C _L = 15pF C _L = 50pF		4.8 6.3	7.7 9.7	1.0 1.0	9.0 11.0	
f _{max}	Maximum Clock Frequency (50% Duty Cycle)	V _{CC} = 3.3 ± 0.3V C _L = 15pF C _L = 50pF	80 50	125 75		70 45		MHz
		V _{CC} = 5.0 ± 0.5V C _L = 15pF C _L = 50pF	130 90	170 115		110 75		
C _{in}	Maximum Input Capacitance			4	10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 1.)	Typical @ 25°C, V _{CC} = 5.0V		pF
		25		

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/2 (per flip-flop). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

TIMING REQUIREMENTS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit		Unit
			T _A = 25°C	T _A = - 40 to 85°C	
t _w	Minimum Pulse Width, CP	3.3 ± 0.3 5.0 ± 0.5	6.0 5.0	7.0 5.0	ns
t _w	Minimum Pulse Width, \bar{RD} or \bar{SD}	3.3 ± 0.3 5.0 ± 0.5	6.0 5.0	7.0 5.0	ns
t _{su}	Minimum Setup Time, D to CP	3.3 ± 0.3 5.0 ± 0.5	6.0 5.0	7.0 5.0	ns
t _h	Minimum Hold Time, D to CP	3.3 ± 0.3 5.0 ± 0.5	0.5 0.5	0.5 0.5	ns
t _{rec}	Minimum Recovery Time, \bar{SD} or \bar{RD} to CP	3.3 ± 0.3 5.0 ± 0.5	5.0 3.0	5.0 3.0	ns

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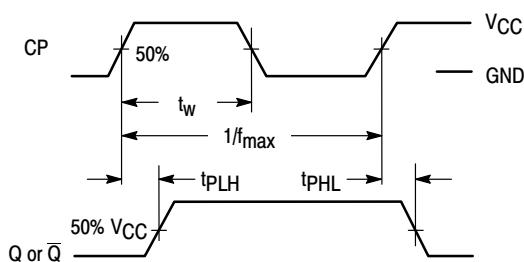


Figure 3.

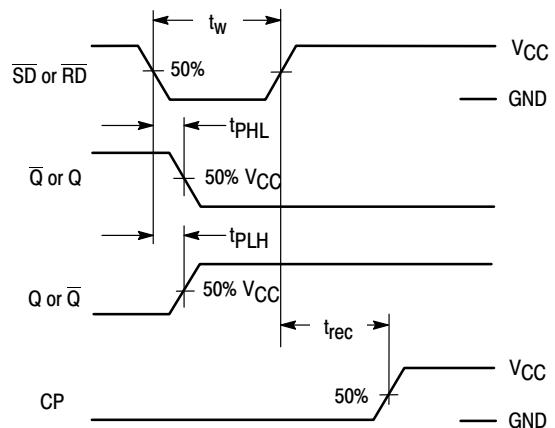


Figure 4.

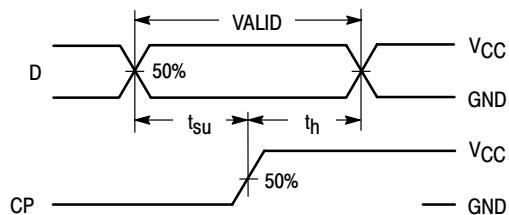
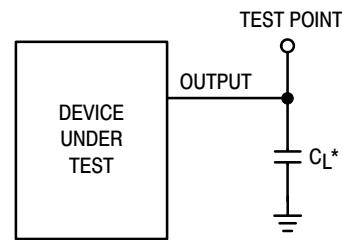


Figure 5.



*Includes all probe and jig capacitance

Switching Waveforms

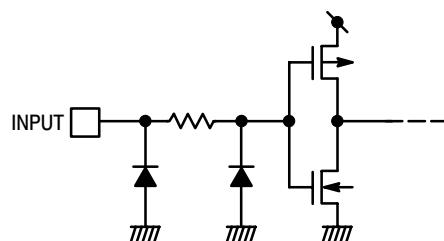


Figure 7. Input Equivalent Circuit